Silicon NPN Power Transistors 2SD526

DESCRIPTION

- ·With TO-220C package
- ·Complement to type 2SB596
- ·Good linearity of h_{FE}

APPLICATIONS

- ·Power amplifier applications
- ·Recommend for 20□25W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

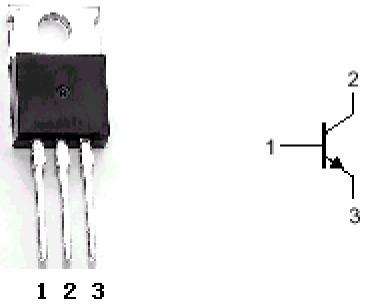

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_B	Base current		0.4	A
P_C	Collector power dissipation	T_C=25□	30	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA; I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3 A;I_B=0.3 A			1.5	V
V_{BE}	Base-emitter voltage	I_C=3A ; V_{CE}=5V			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=80V ;I_E=0			30	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE-1}	DC current gain	I_C=0.5A ; V_{CE}=5V	40		240	
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=5V	15			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=5V		8		MHz
C_{OB}	Output capacitance	I_E=0; V_{CB}=10V;f=1MHz		90		pF

◆ h_{FE-1} classifications

R	O	Y
40-80	70-140	120-240

PACKAGE OUTLINE

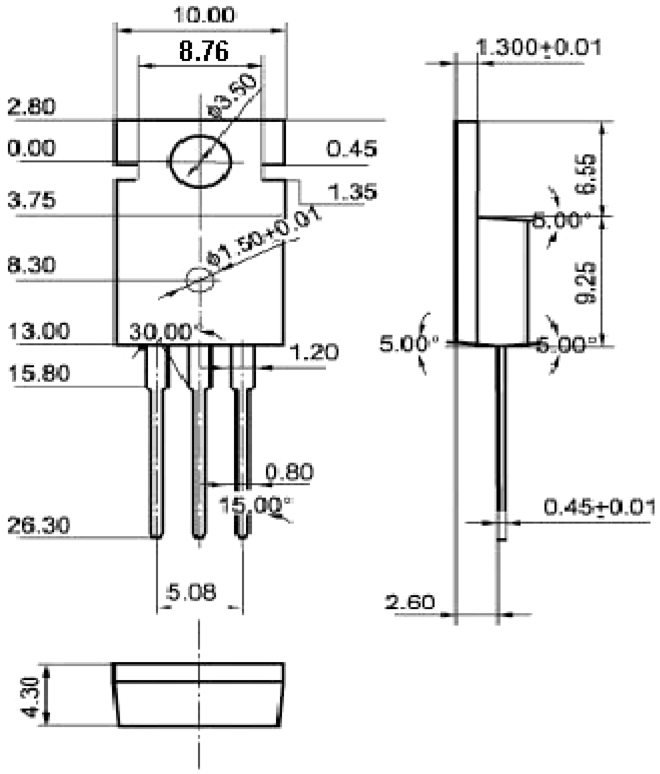

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

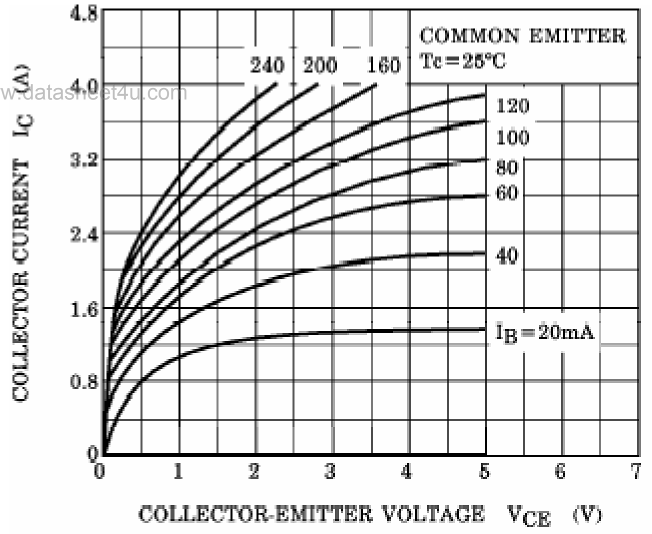

Fig.3 Static Characteristic

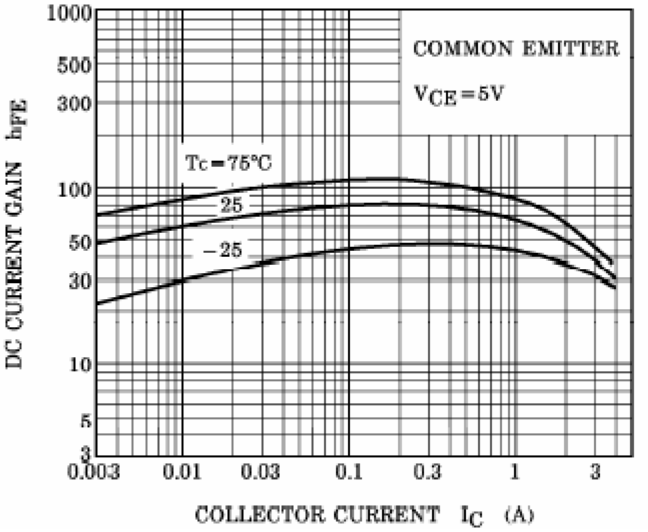

Fig.4 DC current Gain

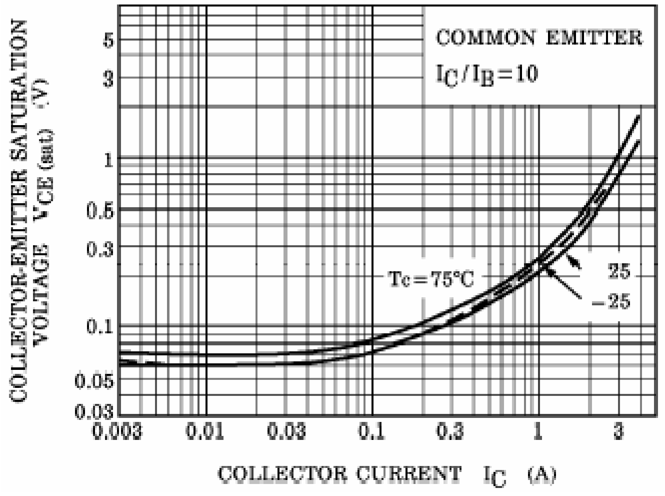

Fig.5 Collector-Emitter Saturation Voltage

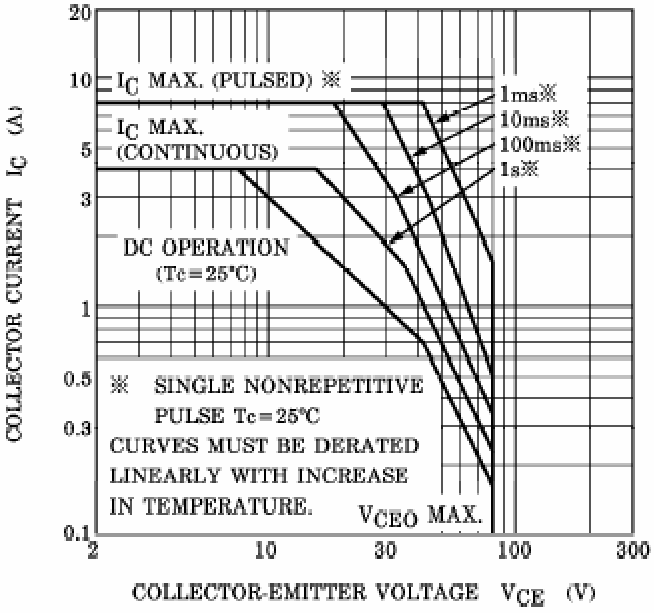

Fig.6 Safe Operating Area